

Fig. 1

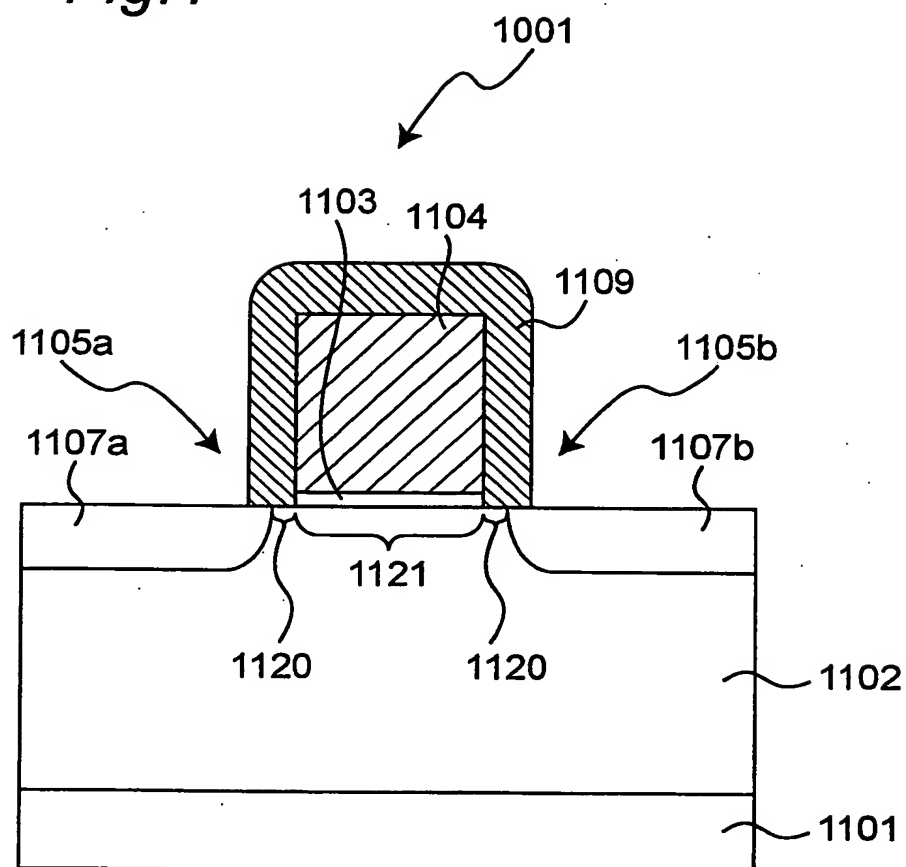


Fig.2A

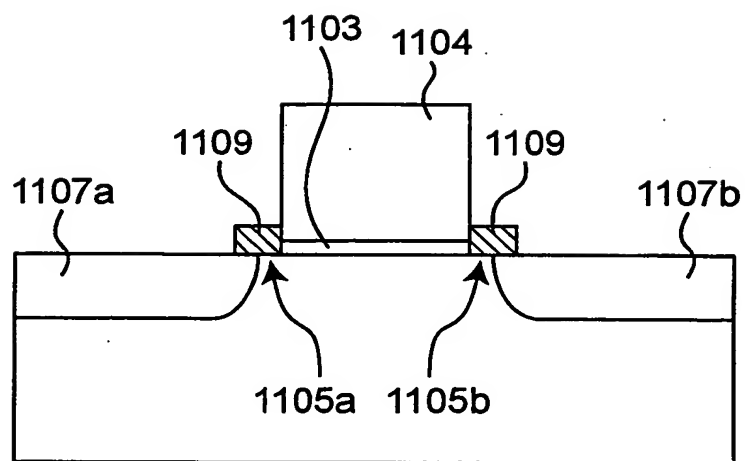


Fig.2B

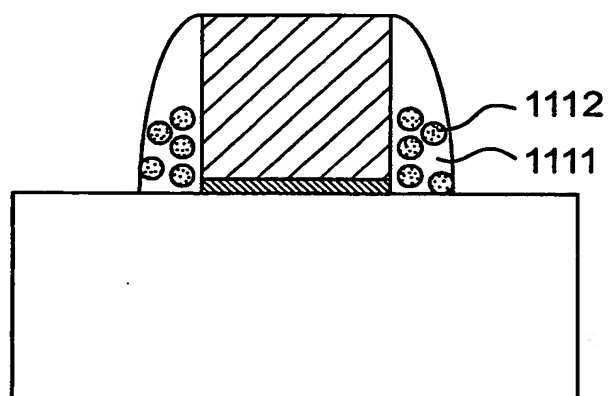


Fig.3

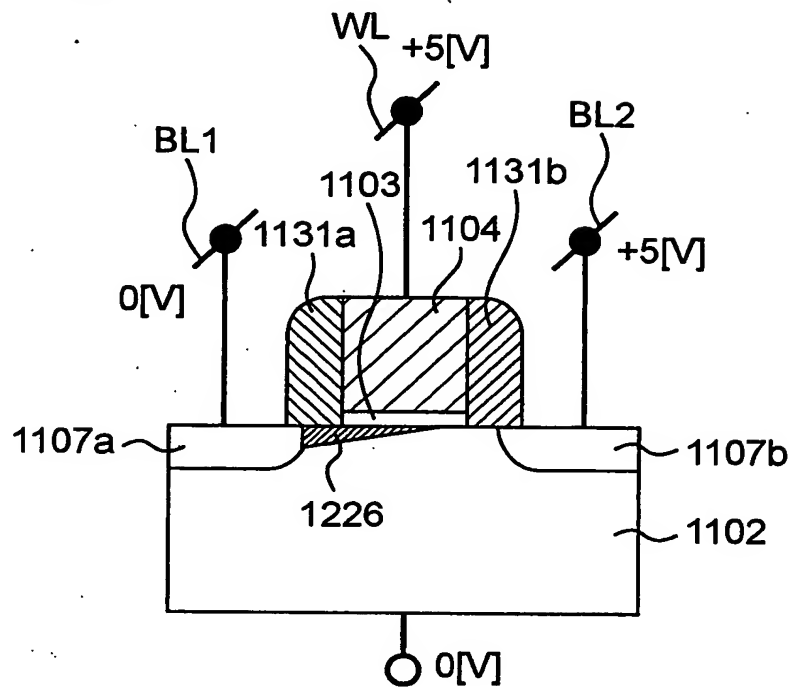


Fig.4

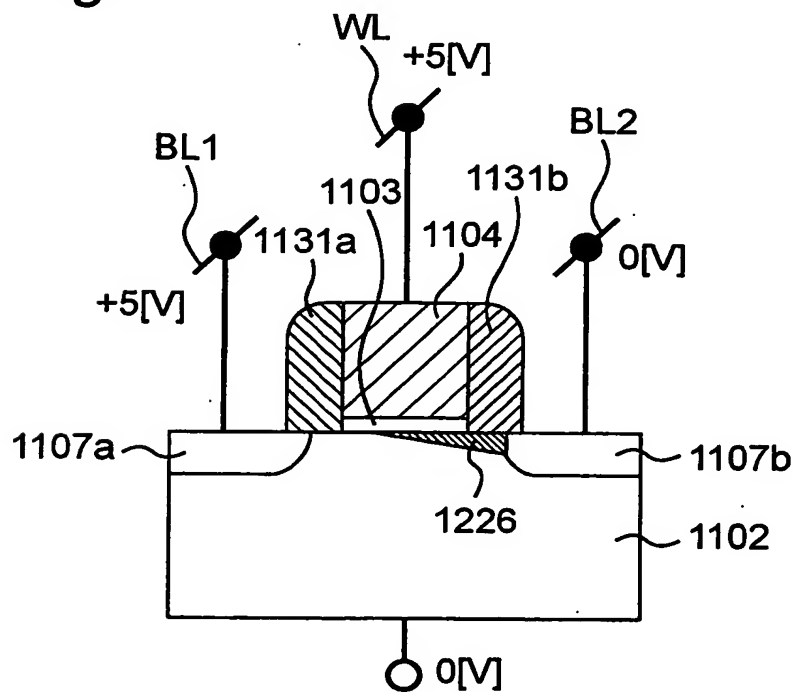


Fig. 5

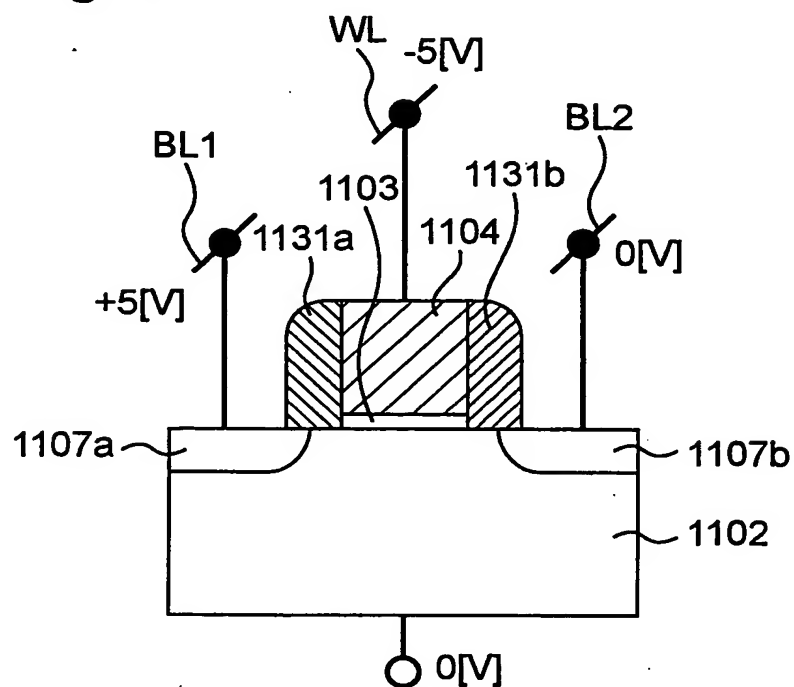


Fig. 6

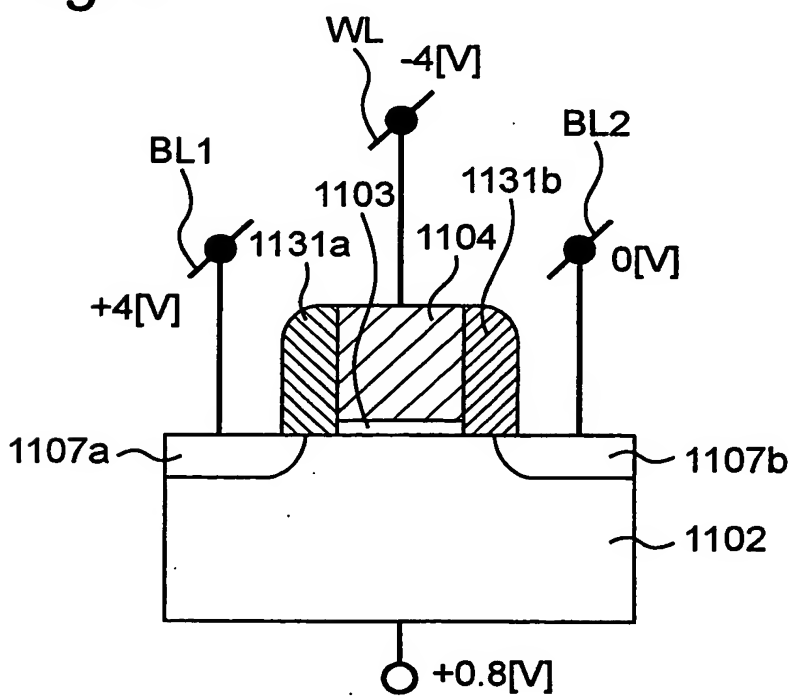


Fig. 7

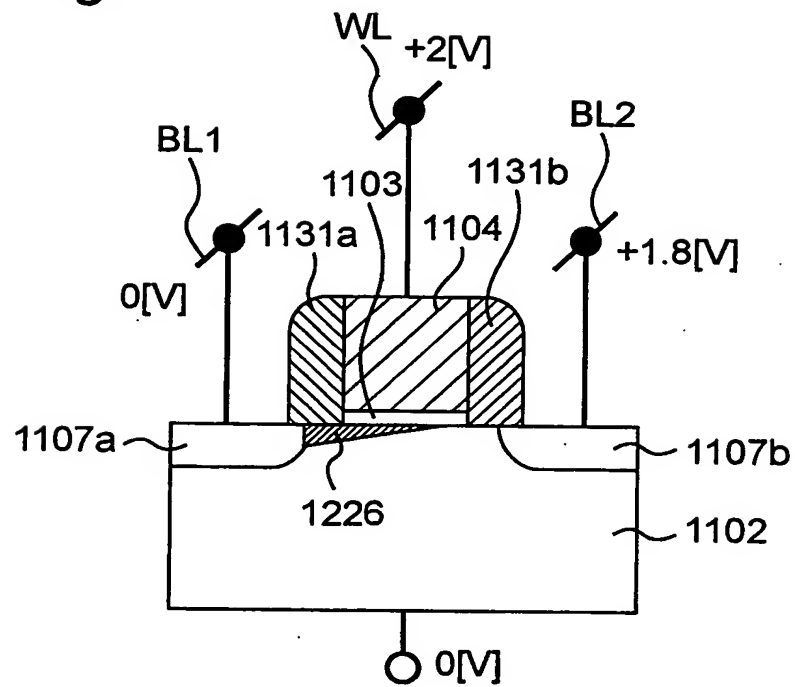
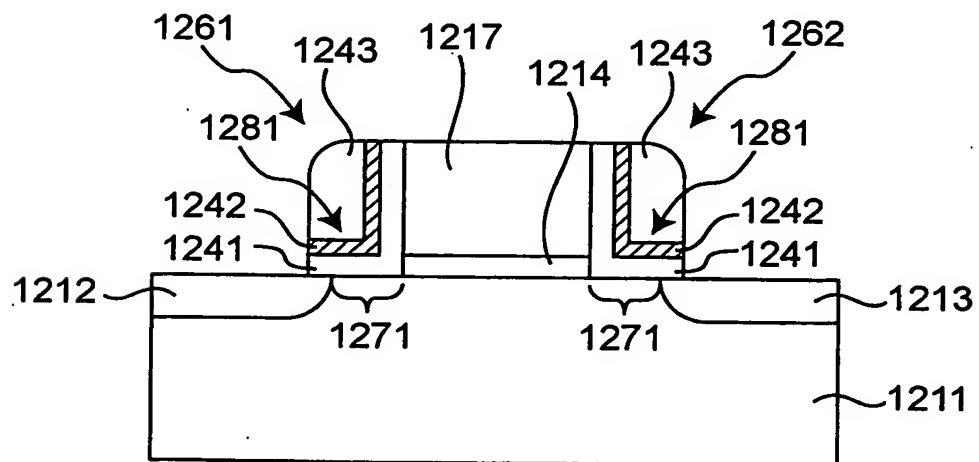


Fig. 8



This cross-sectional view shows a device with a curved top surface 1217. A rectangular feature 1242 is positioned on the surface, with a width $W2$ indicated by a double-headed arrow. The feature has a vertical side 1243 and a horizontal base 1241. A curved surface 1262 is shown on the right side of the feature, and a horizontal surface 1281 is located below it. The device is mounted on a substrate 1211, with a layer 1213 on top. A distance $W1$ is indicated between two vertical dashed lines, and a distance 1271 is indicated between a vertical dashed line and the right edge of the device.

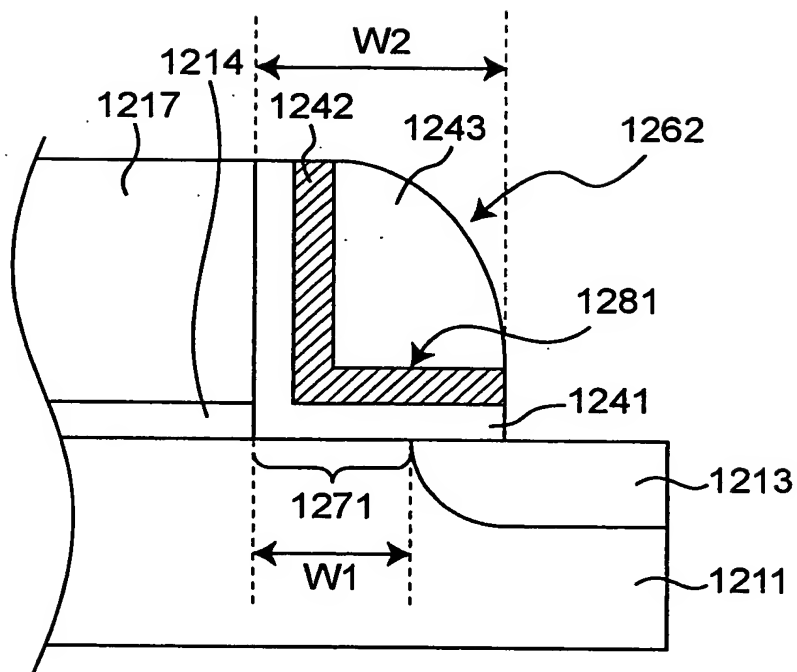


Fig. 10

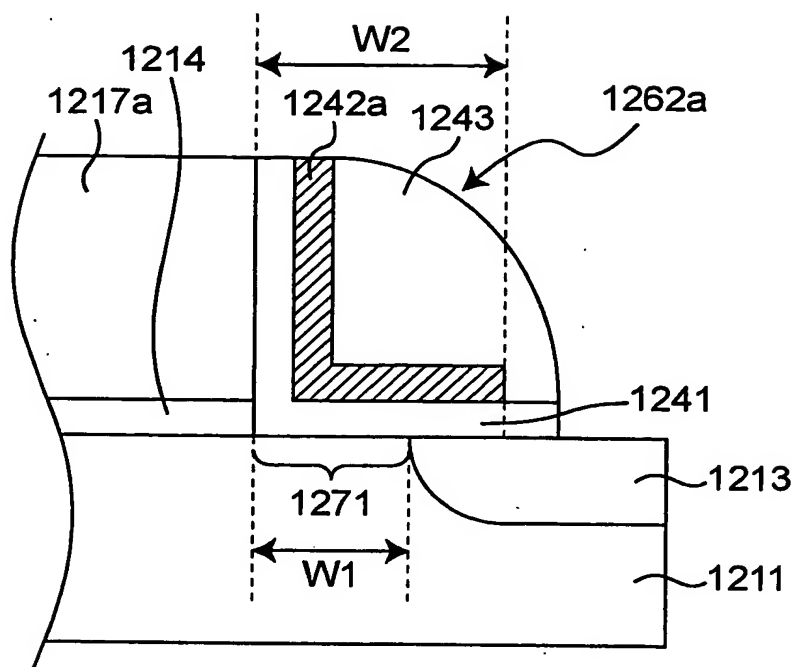


Fig. 11

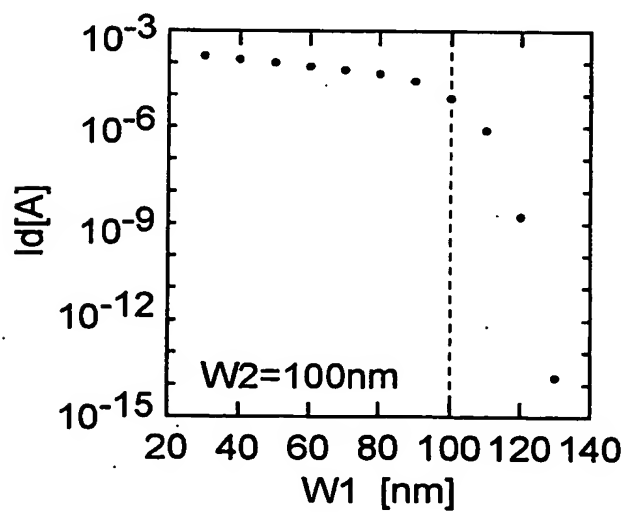


Fig. 12

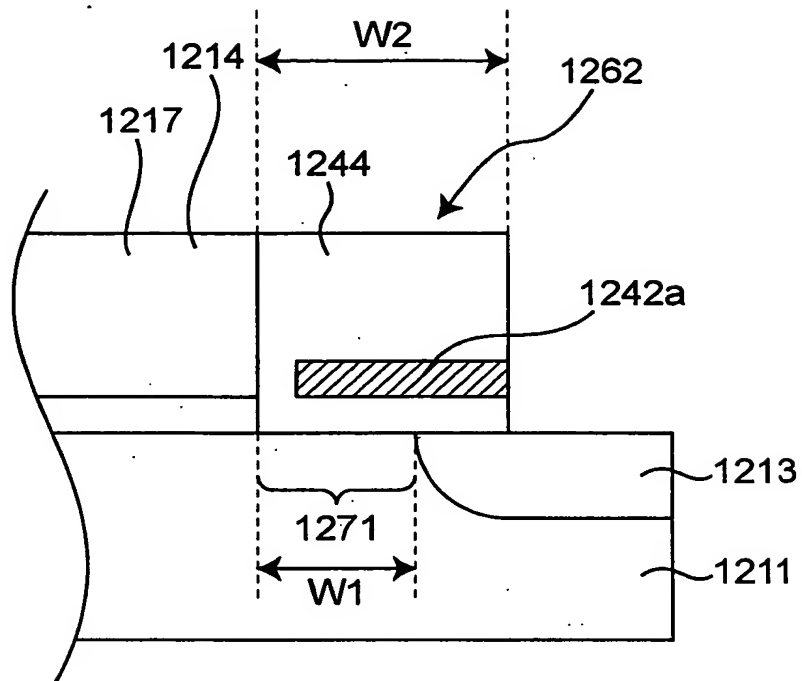
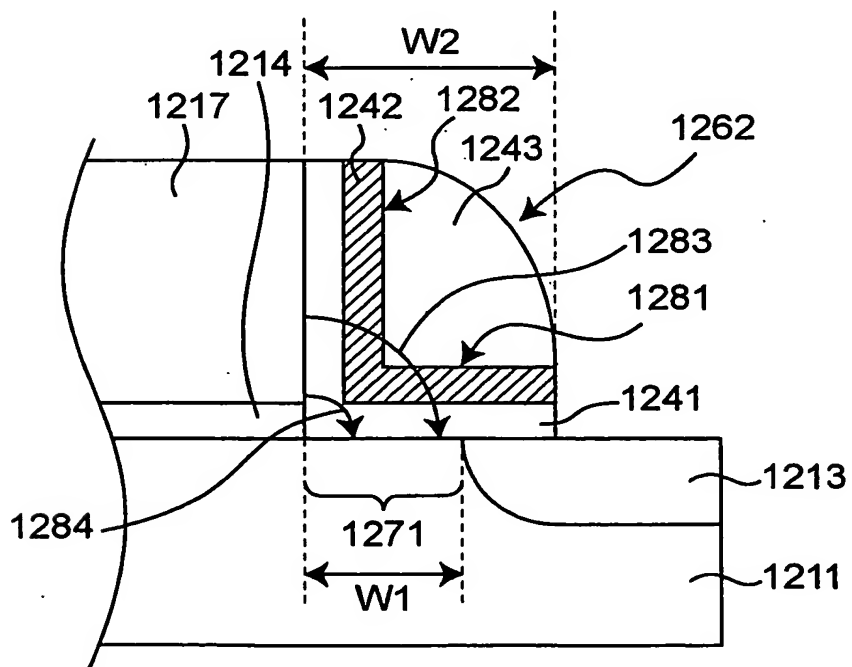


Fig. 13



[illegible]

A cross-sectional view of a semiconductor device. A central channel region 1214 is flanked by two side regions 1212 and 1213. The side regions 1212 and 1213 are further divided into sub-regions 1241 and 1242. The top surface of the device is labeled 1261 and 1262. The bottom surface is labeled 1286, 1287, and 1288. The device is shown in a cross-section with a central channel and side regions.

Fig. 16

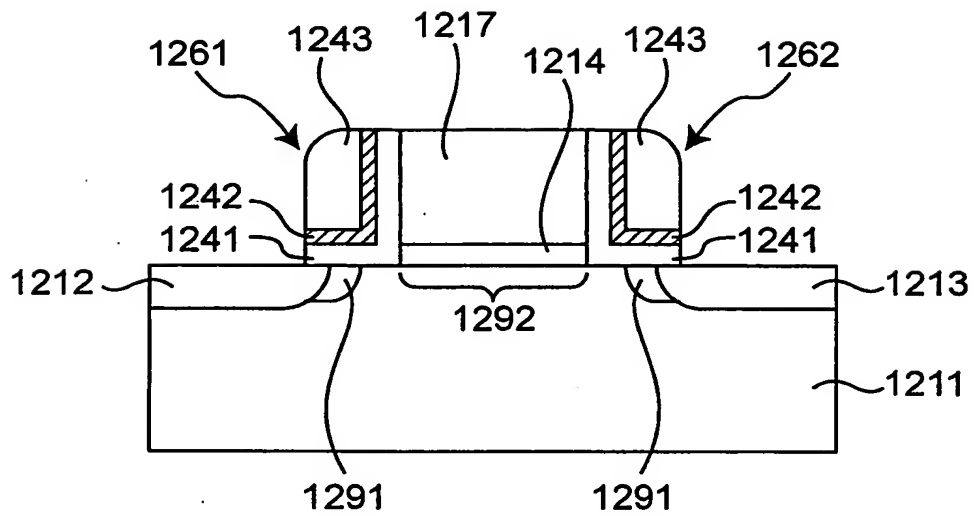


Fig. 17

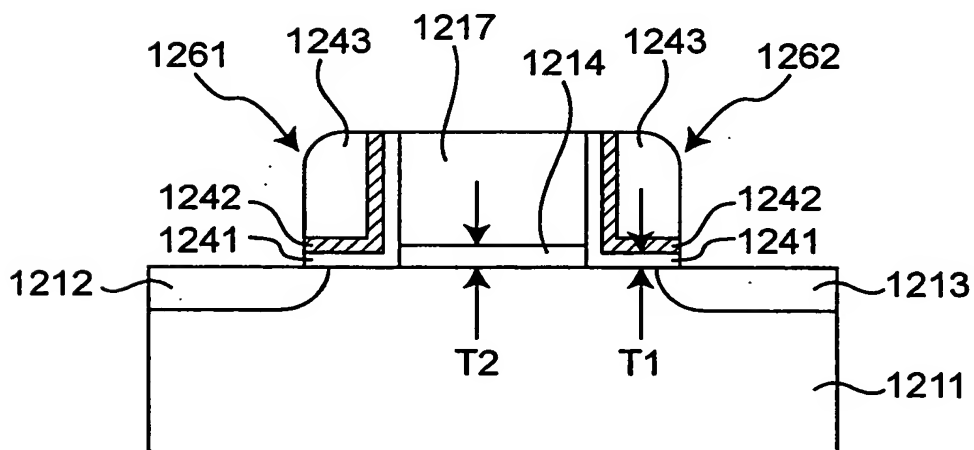


Fig. 18

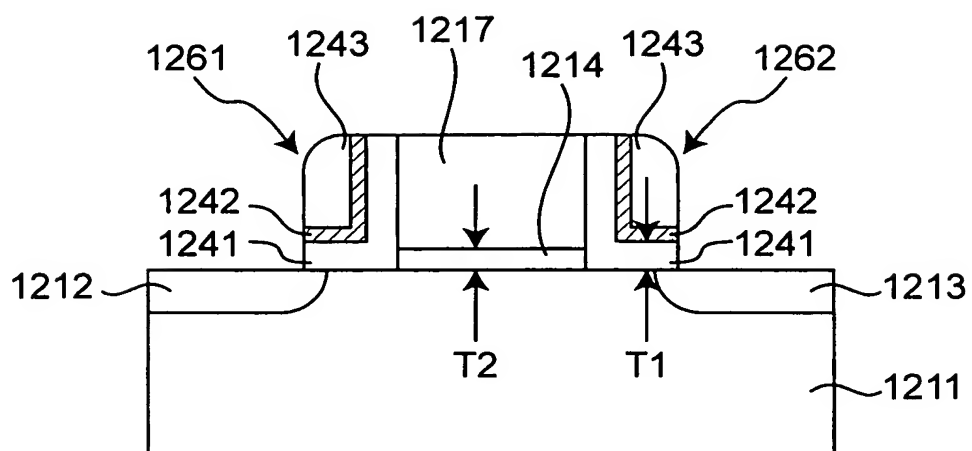


Fig. 19

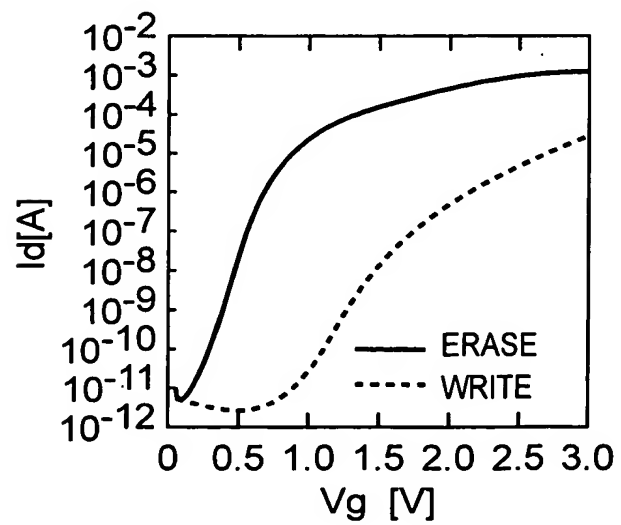


Fig. 20

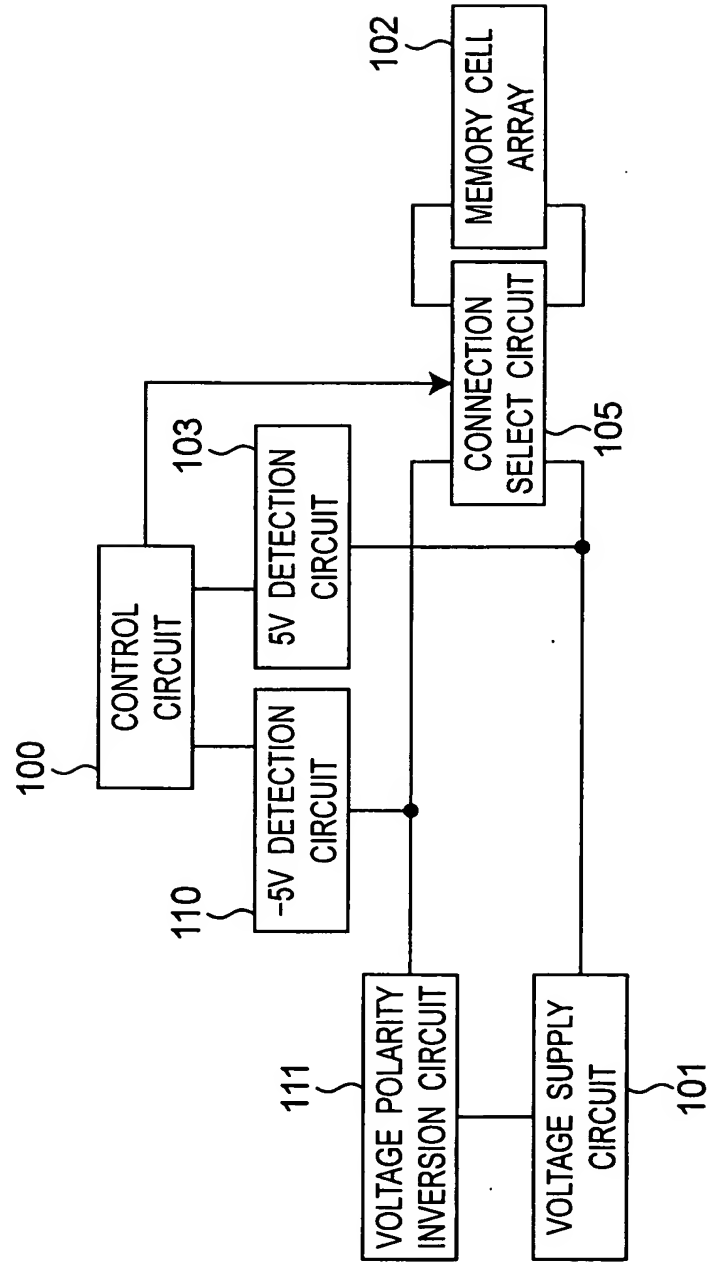


Fig.21

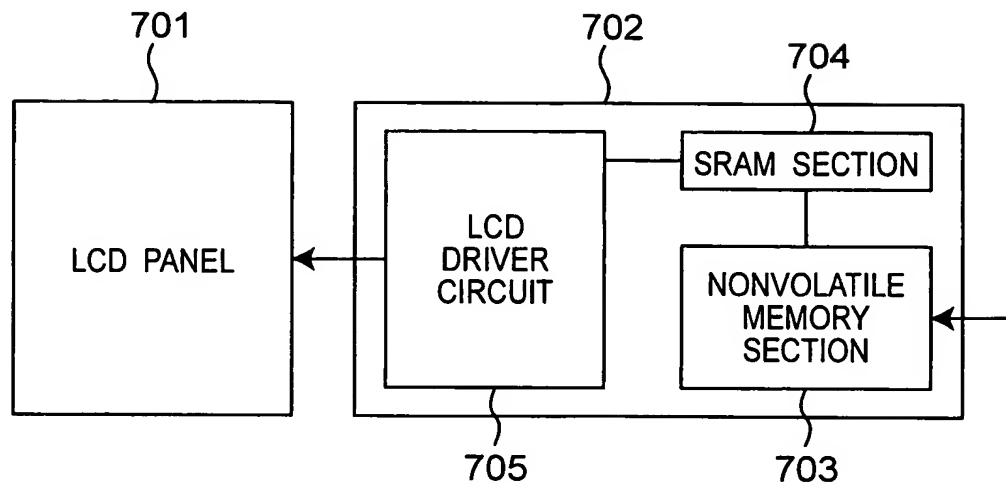


Fig.22

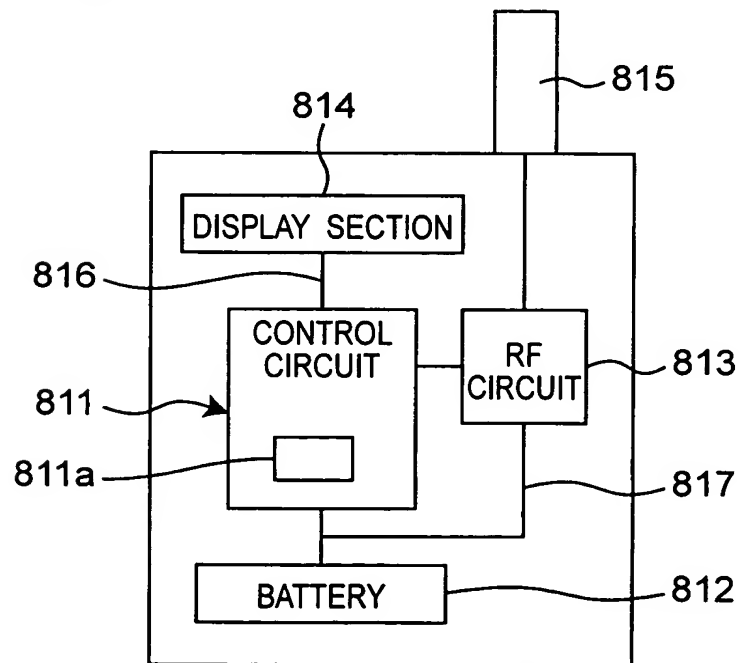


Fig.23 PRIOR ART

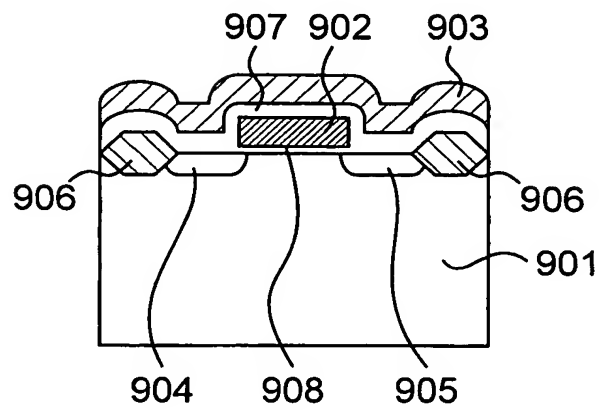


Fig.24 PRIOR ART

